

BLF881; BLF881S

UHF power LDMOS transistor

Rev. 3 — 7 December 2010

Product data sheet

1. Product profile

1.1 General description

A 140 W LDMOS RF power transistor for broadcast transmitter applications and industrial applications. The transistor can deliver 140 W from HF to 1 GHz. The excellent ruggedness and broadband performance of this device makes it ideal for digital transmitter applications.

Table 1. Typical performance

RF performance at $V_{DS} = 50$ V in a common-source 860 MHz test circuit.

Mode of operation	f (MHz)	P_L (W)	$P_{L(PEP)}$ (W)	$P_{L(AV)}$ (W)	G_p (dB)	η_D (%)	IMD3 (dBc)	IMD _{shldr} (dBc)
2-tone, class AB	$f_1 = 860$; $f_2 = 860.1$	-	140	-	21	49	-34	-
DVB-T (8k OFDM)	858	-	-	33	21	34	-	-33 ^[1]

[1] Measured [dBc] with delta marker at 4.3 MHz from center frequency.

CAUTION



This device is sensitive to ElectroStatic Discharge (ESD). Therefore care should be taken during transport and handling.

1.2 Features and benefits

- 2-Tone performance at 860 MHz, a drain-source voltage V_{DS} of 50 V and a quiescent drain current $I_{DQ} = 0.5$ A:
 - ◆ Peak envelope power load power = 140 W
 - ◆ Power gain = 21 dB
 - ◆ Drain efficiency = 49 %
 - ◆ Third order intermodulation distortion = -34 dBc
- DVB performance at 858 MHz, a drain-source voltage V_{DS} of 50 V and a quiescent drain current $I_{DQ} = 0.5$ A:
 - ◆ Average output power = 33 W
 - ◆ Power gain = 21 dB
 - ◆ Drain efficiency = 34 %
 - ◆ Shoulder distance = -33 dBc (4.3 MHz from center frequency)
- Integrated ESD protection
- Excellent ruggedness
- High power gain



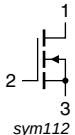
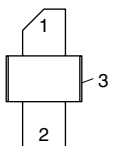
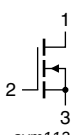
- High efficiency
- Excellent reliability
- Easy power control
- Compliant to Directive 2002/95/EC, regarding Restriction of Hazardous Substances (RoHS)

1.3 Applications

- Communication transmitter applications in the UHF band
- Industrial applications in the UHF band

2. Pinning information

Table 2. Pinning

Pin	Description	Simplified outline	Graphic symbol
BLF881 (SOT467C)			
1	drain		
2	gate		
3	source		
BLF881S (SOT467B)			
1	drain		
2	gate		
3	source		

[1] Connected to flange.

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BLF881	-	flanged LDMOST ceramic package; 2 mounting holes; 2 leads	SOT467C
BLF881S	-	earless LDMOST ceramic package; 2 leads	SOT467B

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage		-	104	V
V_{GS}	gate-source voltage		-0.5	+13	V
T_{stg}	storage temperature		-65	+150	°C
T_j	junction temperature		-	200	°C

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Typ	Unit
$R_{th(j-c)}$	thermal resistance from junction to case	$T_{case} = 80\text{ °C}$; $P_{L(AV)} = 70\text{ W}$	[1]	0.95 K/W

[1] $R_{th(j-c)}$ is measured under RF conditions.

6. Characteristics

Table 6. DC characteristics

$T_j = 25\text{ °C}$ unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{(BR)DSS}$	drain-source breakdown voltage	$V_{GS} = 0\text{ V}$; $I_D = 1.35\text{ mA}$	[1]	104	-	V
$V_{GS(th)}$	gate-source threshold voltage	$V_{DS} = 10\text{ V}$; $I_D = 135\text{ mA}$	[1]	1.4	-	V
I_{DSS}	drain leakage current	$V_{GS} = 0\text{ V}$; $V_{DS} = 50\text{ V}$	-	-	1.4	μA
I_{DSX}	drain cut-off current	$V_{GS} = V_{GSth} + 3.75\text{ V}$; $V_{DS} = 10\text{ V}$	19	21	-	A
I_{GSS}	gate leakage current	$V_{GS} = 10\text{ V}$; $V_{DS} = 0\text{ V}$	-	-	140	nA
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = V_{GSth} + 3.75\text{ V}$; $I_D = 4.5\text{ A}$	[1]	-	210	mΩ
C_{iss}	input capacitance	$V_{GS} = 0\text{ V}$; $V_{DS} = 50\text{ V}$; $f = 1\text{ MHz}$	-	100	-	pF
C_{oss}	output capacitance	$V_{GS} = 0\text{ V}$; $V_{DS} = 50\text{ V}$; $f = 1\text{ MHz}$	-	33.5	-	pF
C_{rss}	reverse transfer capacitance	$V_{GS} = 0\text{ V}$; $V_{DS} = 50\text{ V}$; $f = 1\text{ MHz}$	-	1	-	pF

[1] I_D is the drain current.

Table 7. RF characteristics

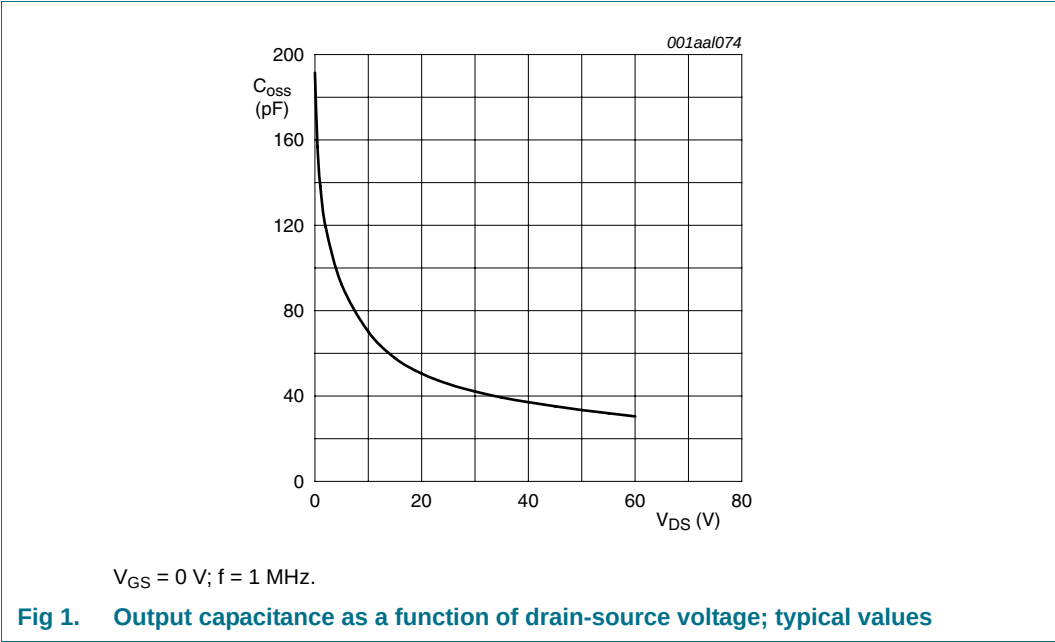
$T_h = 25\text{ °C}$ unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
2-Tone, class AB						
V_{DS}	drain-source voltage		-	50	-	V
I_{Dq}	quiescent drain current		-	0.5	-	A
$P_{L(PEP)}$	peak envelope power load power		-	140	-	W
G_p	power gain		20	21	-	dB
η_D	drain efficiency		45	49	-	%
IMD3	third-order intermodulation distortion		-	-34	-30	dBc

Table 7. RF characteristics ...continued
 $T_h = 25\text{ }^{\circ}\text{C}$ unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
DVB-T (8k OFDM)						
V_{DS}	drain-source voltage		-	50	-	V
I_{DQ}	quiescent drain current		-	0.5	-	A
$P_{L(AV)}$	average output power		-	33	-	W
G_p	power gain		20	21	-	dB
η_D	drain efficiency		30	34	-	%
IMD_{shldr}	intermodulation distortion shoulder	[1]	-	-33	-30	dBc
PAR	peak-to-average ratio	[2]	-	8.3	-	dB

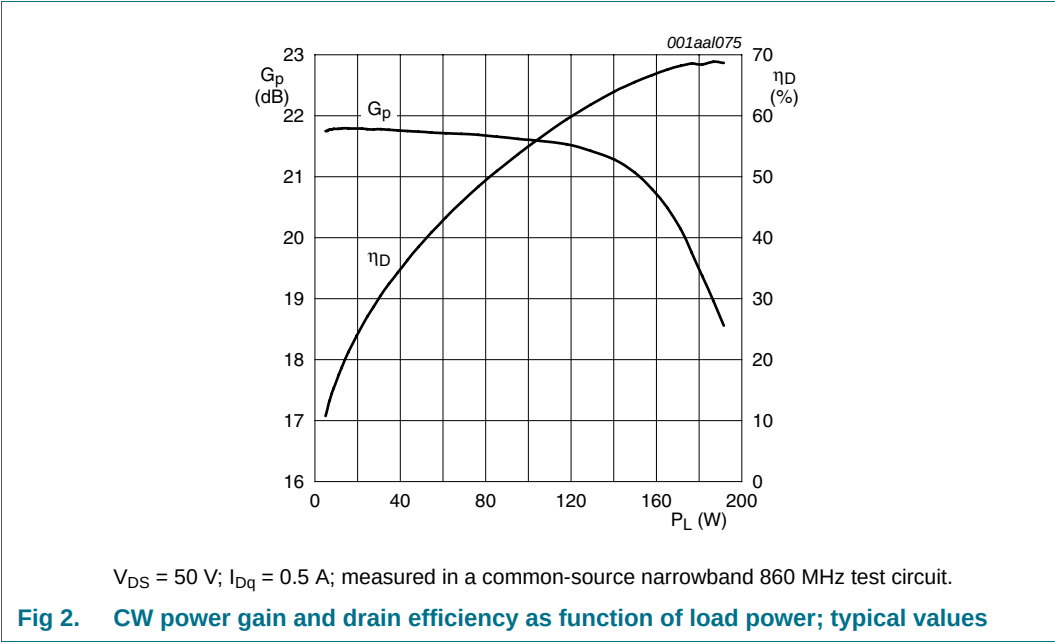
- [1] Measured [dBc] with delta marker at 4.3 MHz from center frequency.
- [2] PAR (of output signal) at 0.01 % probability on CCDF; PAR of input signal = 9.5 dB at 0.01 % probability on CCDF.



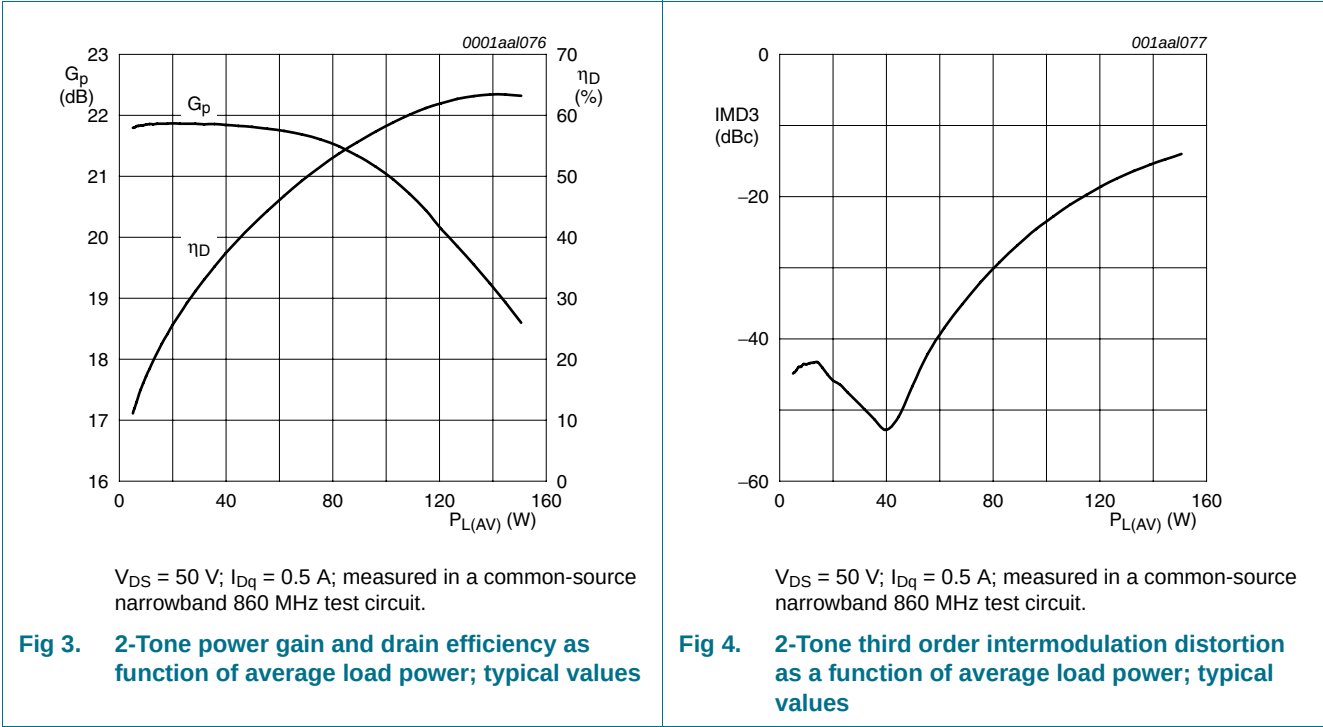
7. Application information

7.1 Narrowband RF figures

7.1.1 CW



7.1.2 2-Tone



7.1.3 DVB-T

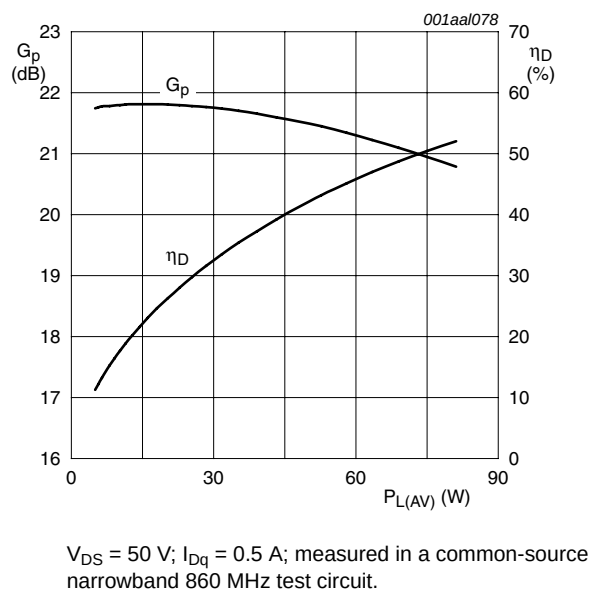


Fig 5. DVB-T power gain and drain efficiency as function of average load power; typical values

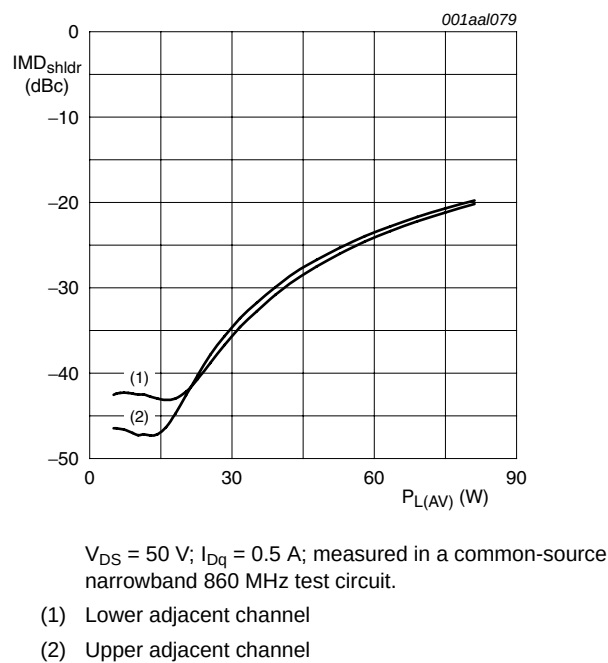
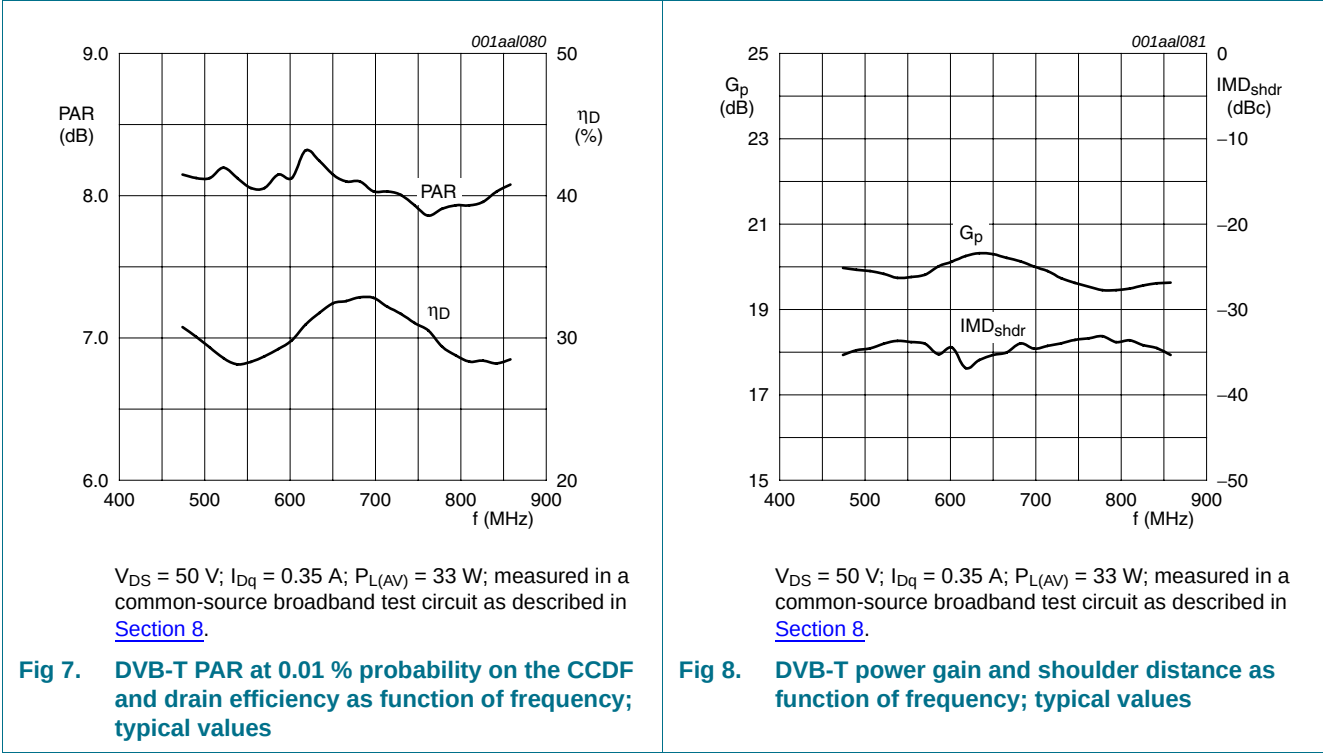


Fig 6. DVB-T shoulder distance as a function of average load power; typical values

7.2 Broadband RF figures

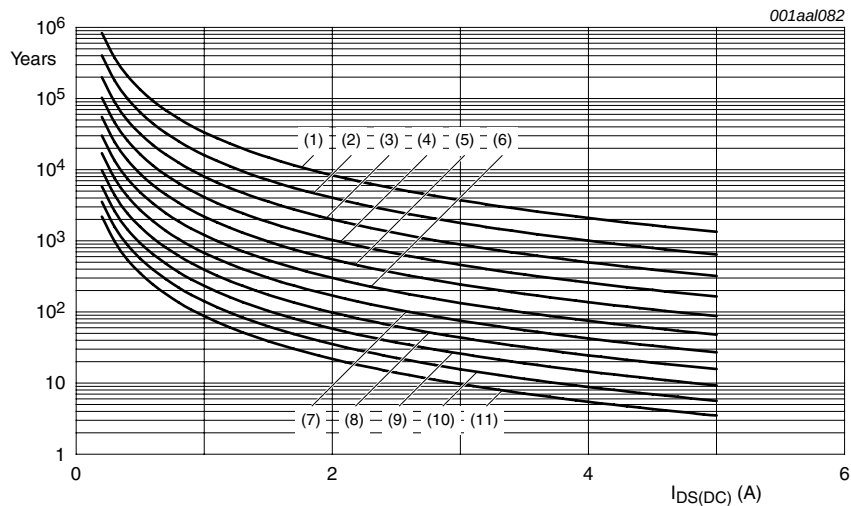
7.2.1 DVB-T



7.3 Ruggedness in class-AB operation

The BLF881 and BLF881S are capable of withstanding a load mismatch corresponding to VSWR = 10 : 1 through all phases under the following conditions: $V_{DS} = 50\text{ V}$; $f = 860\text{ MHz}$ at rated power. Ruggedness is measured in the application circuit as described in [Section 8](#).

7.4 Reliability



TTF (0.1 % failure fraction).

The reliability at pulsed conditions can be calculated as follows: $TTF (0.1\%) \times 1 / \delta$.

- (1) $T_j = 100\text{ }^{\circ}\text{C}$
- (2) $T_j = 110\text{ }^{\circ}\text{C}$
- (3) $T_j = 120\text{ }^{\circ}\text{C}$
- (4) $T_j = 130\text{ }^{\circ}\text{C}$
- (5) $T_j = 140\text{ }^{\circ}\text{C}$
- (6) $T_j = 150\text{ }^{\circ}\text{C}$
- (7) $T_j = 160\text{ }^{\circ}\text{C}$
- (8) $T_j = 170\text{ }^{\circ}\text{C}$
- (9) $T_j = 180\text{ }^{\circ}\text{C}$
- (10) $T_j = 190\text{ }^{\circ}\text{C}$
- (11) $T_j = 200\text{ }^{\circ}\text{C}$

Fig 9. BLF881 electromigration

8. Test information

Table 8. List of components

For test circuit, see [Figure 10](#), [Figure 11](#) and [Figure 12](#).

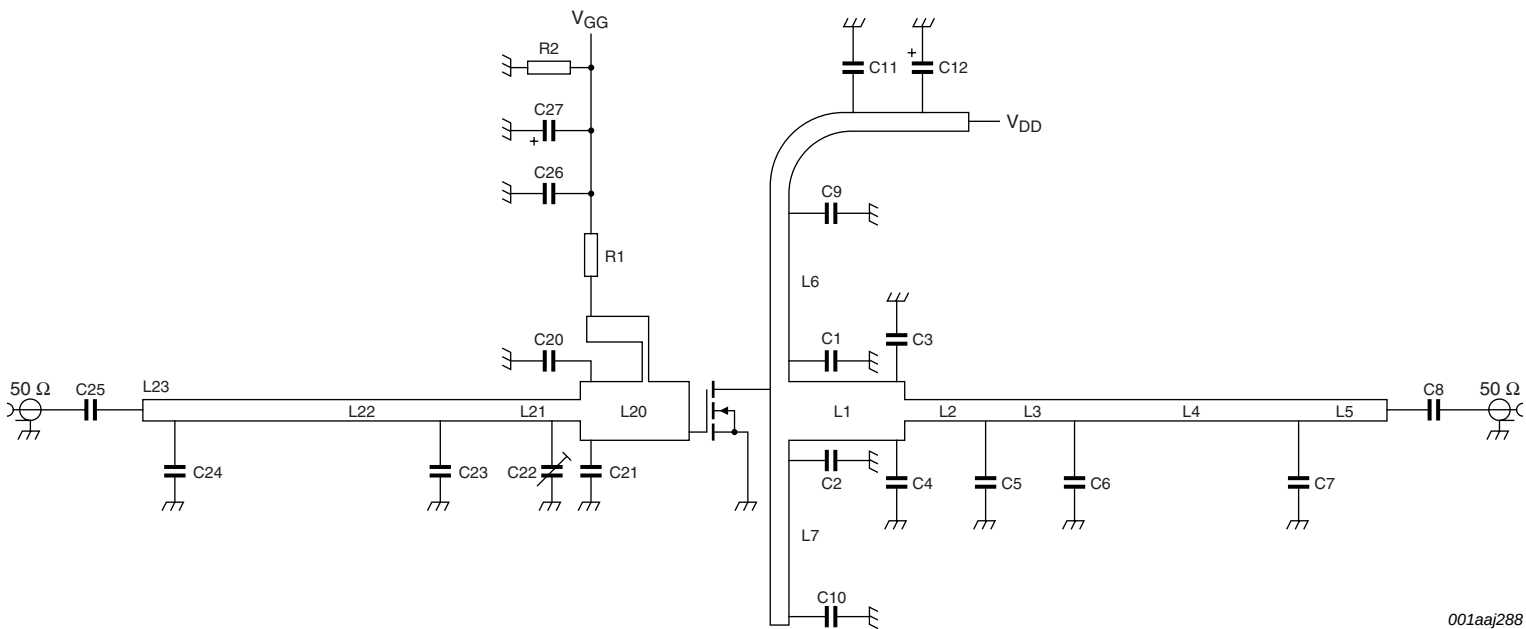
Component	Description	Value	Remarks
C1, C2	multilayer ceramic chip capacitor	5.1 pF	[1]
C3, C4	multilayer ceramic chip capacitor	10 pF	[2]
C5	multilayer ceramic chip capacitor	6.8 pF	[1]
C6	multilayer ceramic chip capacitor	4.7 pF	[1]
C7	multilayer ceramic chip capacitor	2.7 pF	[1]
C8, C9, C10, C25, C26	multilayer ceramic chip capacitor	100 pF	[1]
C11, C27	multilayer ceramic chip capacitor	10 μ F	TDK C570X7R1H106KT000N or capacitor of same quality.
C12	electrolytic capacitor	470 μ F; 63 V	
C20	multilayer ceramic chip capacitor	10 pF	[3]
C21	multilayer ceramic chip capacitor	8.2 pF	[3]
C22	trimmer	0.6 pF to 4.5 pF	Tekelec
C23	multilayer ceramic chip capacitor	6.8 pF	[3]
C24	multilayer ceramic chip capacitor	3.9 pF	[3]
L1	stripline	-	[4] (W $\times$ L) 7 mm $\times$ 15 mm
L2	stripline	-	[4] (W $\times$ L) 2.4 mm $\times$ 9 mm
L3	stripline	-	[4] (W $\times$ L) 2.4 mm $\times$ 10 mm
L4	stripline	-	[4] (W $\times$ L) 2.4 mm $\times$ 25 mm
L5	stripline	-	[4] (W $\times$ L) 2.4 mm $\times$ 10 mm
L6	stripline	-	[4] (W $\times$ L) 2.0 mm $\times$ 20 mm
L7	stripline	-	[4] (W $\times$ L) 2.0 mm $\times$ 21 mm
L20	stripline	-	[4] (W $\times$ L) 7 mm $\times$ 12 mm
L21	stripline	-	[4] (W $\times$ L) 2.4 mm $\times$ 13 mm
L22	stripline	-	[4] (W $\times$ L) 2.4 mm $\times$ 31 mm
L23	stripline	-	[4] (W $\times$ L) 2.4 mm $\times$ 5 mm
R1	resistor	100 Ω	
R2	resistor	10 k Ω	

[1] American technical ceramics type 100B or capacitor of same quality.

[2] American technical ceramics type 180R or capacitor of same quality.

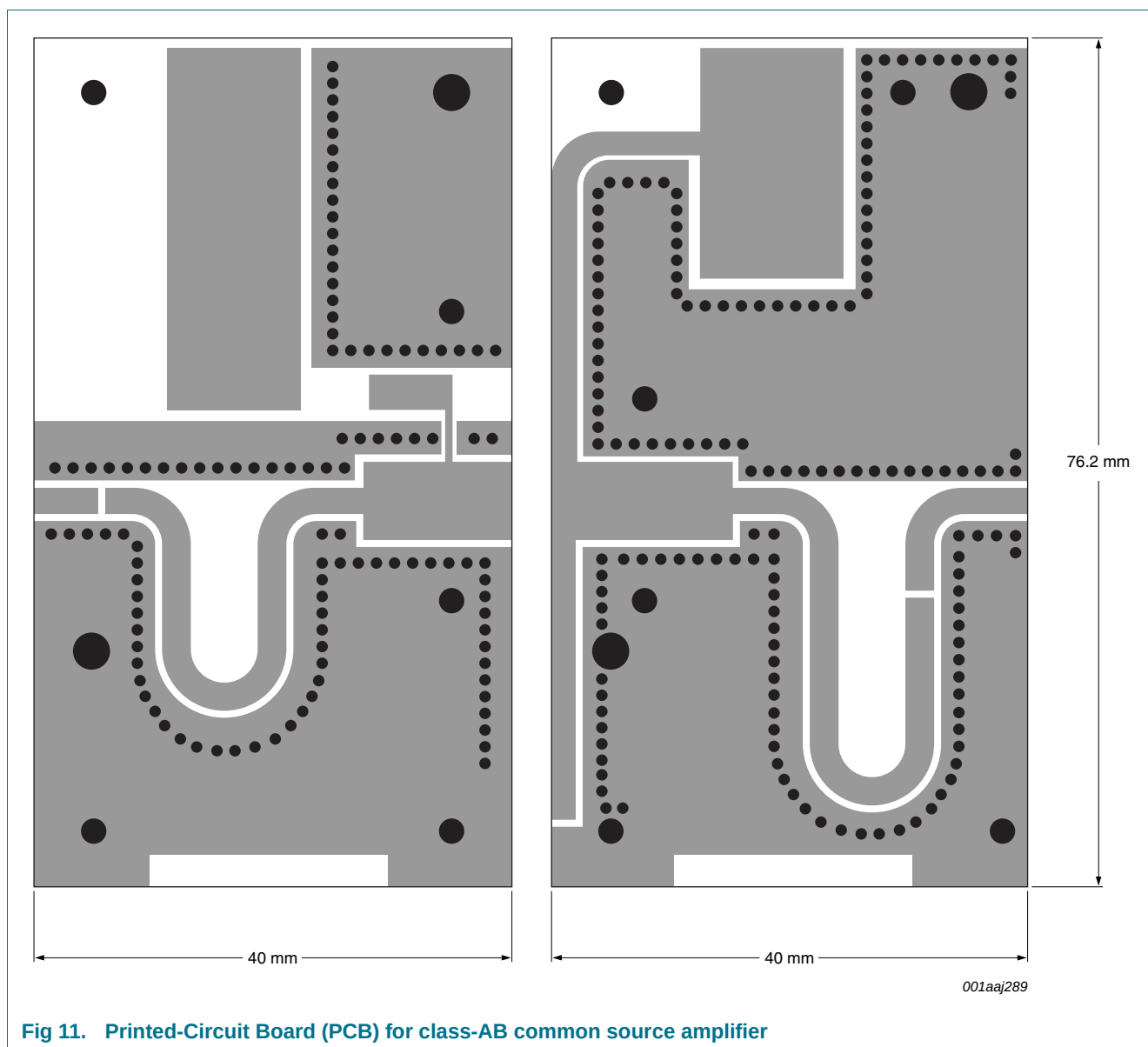
[3] American technical ceramics type 100A or capacitor of same quality.

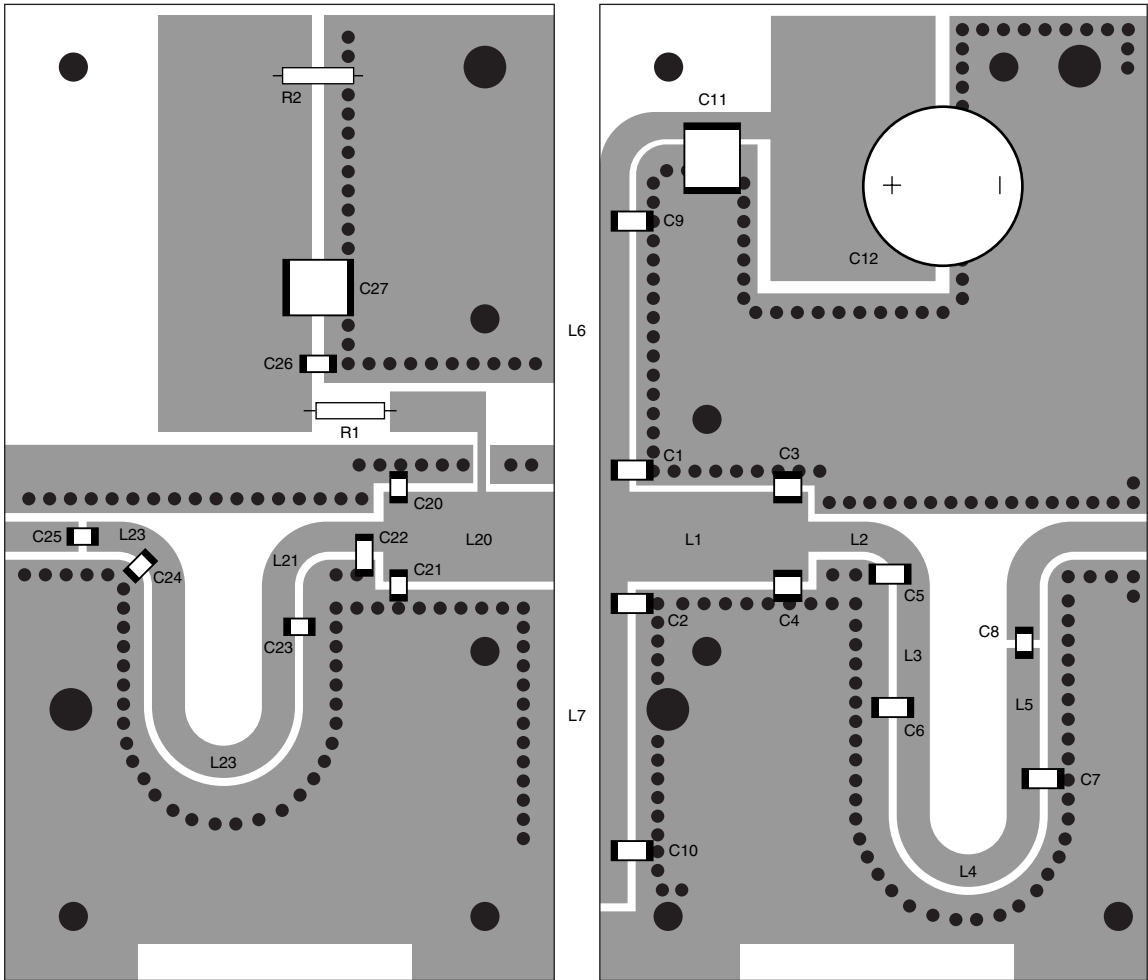
[4] Printed-Circuit Board (PCB): Rogers 5880; $\epsilon_r = 2.2$ F/m; height = 0.79 mm; Cu (top/bottom metallization); thickness copper plating = 35 μ m.



See [Table 8](#) for a list of components.

Fig 10. Class-AB common-source broadband amplifier





001aa/290

See [Table 8](#) for a list of components.

Fig 12. Component layout for class-AB common source amplifier

9. Package outline

Flanged LDMOST ceramic package; 2 mounting holes; 2 leads

SOT467C

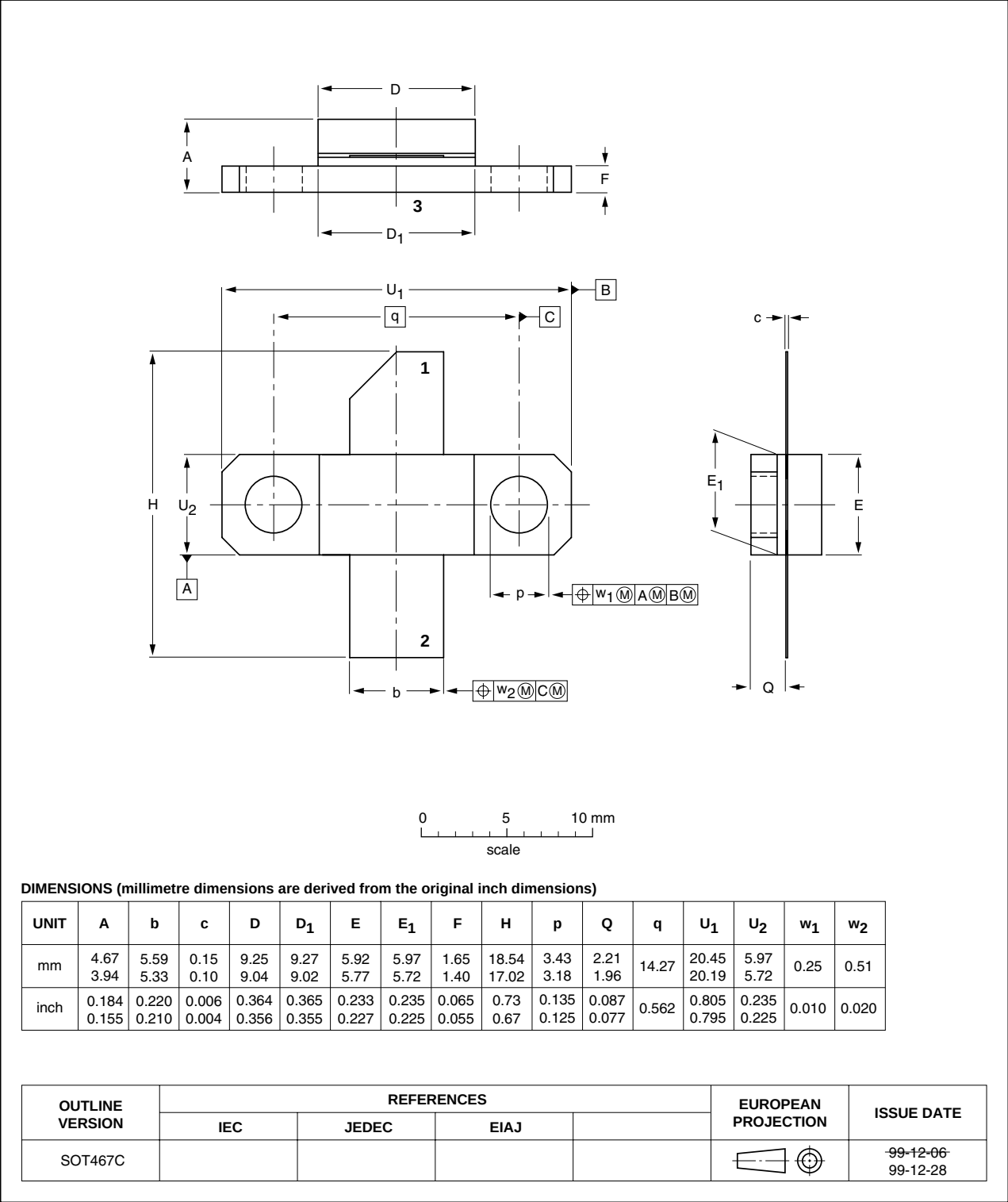


Fig 13. Package outline SOT467C

Earless LDMOST ceramic package; 2 leads

SOT467B

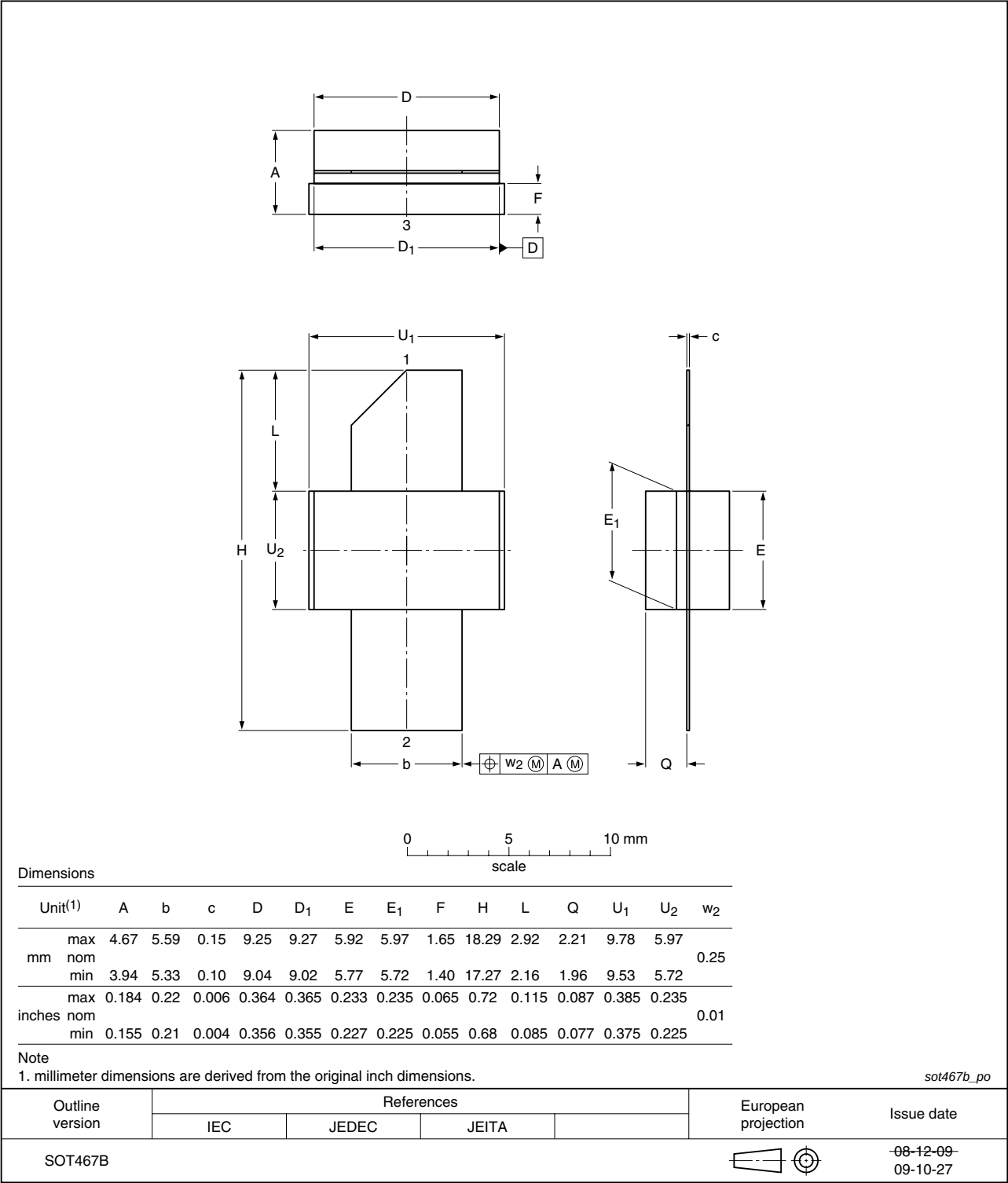


Fig 14. Package outline SOT467B

10. Abbreviations

Table 9. Abbreviations

Acronym	Description
CW	Continuous Wave
CCDF	Complementary Cumulative Distribution Function
DVB	Digital Video Broadcast
DVB-T	Digital Video Broadcast - Terrestrial
ESD	ElectroStatic Discharge
HF	High Frequency
IMD3	Third order InterModulation Distortion
LDMOS	Laterally Diffused Metal-Oxide Semiconductor
LDMOST	Laterally Diffused Metal-Oxide Semiconductor Transistor
OFDM	Orthogonal Frequency Division Multiplexing
PAR	Peak-to-Average power Ratio
PEP	Peak Envelope Power
RF	Radio Frequency
TTF	Time To Failure
UHF	Ultra High Frequency
VSWR	Voltage Standing-Wave Ratio

11. Revision history

Table 10. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BLF881_BLF881S v.3	20101207	Product data sheet	-	BLF881_BLF881S v.2
Modifications:	• Table 6 on page 3 : In the conditions column of $V_{GS(th)}$ the value of I_D has been changed			
BLF881_BLF881S v.2	20100210	Product data sheet	-	BLF881_BLF881S v.1
BLF881_BLF881S v.1	20091210	Preliminary data sheet	-	-

12. Legal information

12.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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[2] The term 'short data sheet' is explained in section "Definitions".

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14. Contents

1	Product profile	1
1.1	General description	1
1.2	Features and benefits	1
1.3	Applications	2
2	Pinning information	2
3	Ordering information	2
4	Limiting values	3
5	Thermal characteristics	3
6	Characteristics	3
7	Application information	5
7.1	Narrowband RF figures	5
7.1.1	CW	5
7.1.2	2-Tone	5
7.1.3	DVB-T	6
7.2	Broadband RF figures	7
7.2.1	DVB-T	7
7.3	Ruggedness in class-AB operation	7
7.4	Reliability	8
8	Test information	9
9	Package outline	13
10	Abbreviations	15
11	Revision history	15
12	Legal information	16
12.1	Data sheet status	16
12.2	Definitions	16
12.3	Disclaimers	16
12.4	Licenses	17
12.5	Trademarks	17
13	Contact information	17
14	Contents	18

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